

HybridPACK™ 1 Module

FS400R07A3E3

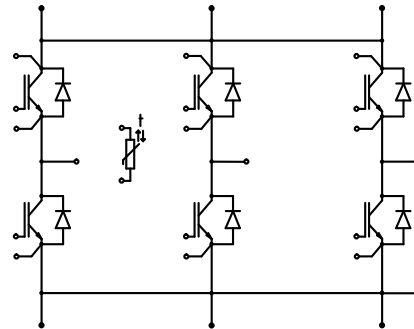
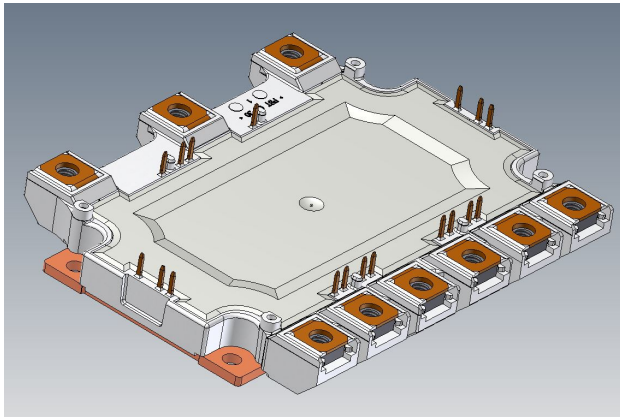
Final Data Sheet

V3.0, 2017-03-07

Automotive High Power

1 Features / Description

HybridPACK™ 1 module with Trench/Fieldstop IGBT3 and Emitter Controlled 3 diode and NTC



$V_{CES} = 700V$

$I_{C\ nom} = 400A / I_{CRM} = 800A$

Typical Applications

- Hybrid Electrical Vehicles (H)EV
- Motor Drives
- Optimized for automotive applications with DC link voltages up to 450 V

Electrical Features

- Increased blocking voltage capability to 705V
- V_{CESat} with positive Temperature Coefficient
- LOW V_{CESat}
- Low Switching Losses
- Low Inductive Design
- $T_{vj\ op} = 150^{\circ}C$
- Short-time extended Operation Temperature
 $T_{vj\ op} = 175^{\circ}C$

Mechanical Features

- 2.5kV AC 1min Insulation
- Al_2O_3 Substrate with Low Thermal Resistance
- Copper Base Plate
- Integrated NTC temperature sensor
- High mechanical robustness
- RoHS compliant

Description

Infineon's HybridPACK™ 1 DC6 is a variant of the HybridPACK™ 1 power module family with increased continuous current capability and a reduced stray inductance.

Like all HybridPACK™ 1 products the HybridPACK™ 1 DC6 is an automotive qualified powermodule designed for electric vehicle applications. Designed for a 150°C junction operation temperature, with a 30 hour limited 175°C capacity the module accommodates a 3-phase Six-Pack configuration of Trench-Field-Stop IGBT3 and matching emitter controlled diodes. The HybridPACK™ 1 power module family is built on Infineon's long time experience in the development of IGBT power modules, intense research efforts of new material combinations and assembly technologies. HybridPACK™ 1 DC6 is suitable for air or liquid cooling. The copper base plate combined with high-performance ceramic substrate and Infineon's enhanced wire-bonding process provides unparalleled thermal and power cycling capability and highest reliability for mild hybrid inverter or generator applications. For a compact design the driver stage PCB can easily be soldered on top of the module. All power connections are realized with screw terminals.

Product Name	Ordering Code
FS400R07A3E3	

2 IGBT, Inverter

2.1 Maximum Rated Values

Parameter	Conditions	Symbol	Value	Unit
Collector-emitter voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{CES}	705	V
Continuous DC collector current	$T_C = 65^{\circ}\text{C}, T_{vj\text{ max}} = 175^{\circ}\text{C}$ $T_C = 25^{\circ}\text{C}, T_{vj\text{ max}} = 175^{\circ}\text{C}$	$I_{C\text{ nom}}$ I_C	400 ¹⁾ 500 ¹⁾	A A
Maximum RMS module terminal current	$T_F = 25^{\circ}\text{C}, T_{Ct} = 150^{\circ}\text{C}$	I_{RMS}	320 ²⁾	A
Repetitive peak collector current	$t_p = 1\text{ ms}$	I_{CRM}	800	A
Total power dissipation	$T_C = 25^{\circ}\text{C}, T_{vj\text{ max}} = 175^{\circ}\text{C}$	P_{tot}	1250	W
Gate-emitter peak voltage		V_{GES}	+/-20	V

2.2 Characteristic Values

Parameter	Conditions	Symbol	min. typ. max.			Unit	
Collector-emitter saturation voltage	$I_C = 400\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 400\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 400\text{ A}, V_{GE} = 15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$V_{CE\text{ sat}}$	1.45 1.60 1.70	1.70	V	
Gate threshold voltage	$I_C = 6.40\text{ mA}, V_{CE} = V_{GE}$	$T_{vj} = 25^{\circ}\text{C}$	$V_{GE\text{ th}}$	4.90	5.80	6.50	V
Gate charge	$V_{GE} = -15\text{ V} \dots 15\text{ V}$		Q_G	4.30		μC	
Internal gate resistor		$T_{vj} = 25^{\circ}\text{C}$	R_{Gint}	1.0		Ω	
Input capacitance	$f = 1\text{ MHz}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$	C_{ies}	26.0		nF	
Reverse transfer capacitance	$f = 1\text{ MHz}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$	C_{res}	0.76		nF	
Collector-emitter cut-off current	$V_{CE} = 450\text{ V}, V_{GE} = 0\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$	I_{CES}		0.1	mA	
Gate-emitter leakage current	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$	I_{GES}		400	nA	
Turn-on delay time, inductive load	$I_C = 400\text{ A}, V_{CE} = 300\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 1.8\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$t_{d\text{ on}}$	0.12 0.12 0.12		μs	
Rise time, inductive load	$I_C = 400\text{ A}, V_{CE} = 300\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 1.8\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_r	0.08 0.08 0.08		μs	
Turn-off delay time, inductive load	$I_C = 400\text{ A}, V_{CE} = 300\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 1.8\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$t_{d\text{ off}}$	0.36 0.40 0.40		μs	
Fall time, inductive load	$I_C = 400\text{ A}, V_{CE} = 300\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 1.8\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_f	0.02 0.03 0.03		μs	
Turn-on energy loss per pulse	$I_C = 400\text{ A}, V_{CE} = 300\text{ V}, L_S = 16\text{ nH}$ $V_{GE} = \pm 15\text{ V}, di/dt = 4500\text{ A}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{Gon} = 1.8\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{on}	5.10 6.80 7.30		mJ	
Turn-off energy loss per pulse	$I_C = 400\text{ A}, V_{CE} = 300\text{ V}, L_S = 16\text{ nH}$ $V_{GE} = \pm 15\text{ V}, du/dt = 3400\text{ V}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{Goff} = 1.8\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{off}	9.10 12.0 12.5		mJ	
SC data	$V_{GE} \leq 15\text{ V}, V_{CC} = 360\text{ V}$ $V_{CE\text{ max}} = V_{CES} - L_{SCE} \cdot di/dt$	$t_p \leq 8\ \mu\text{s}, T_{vj} = 25^{\circ}\text{C}$ $t_p \leq 6\ \mu\text{s}, T_{vj} = 150^{\circ}\text{C}$	I_{SC}	2800 2000		A	
Thermal resistance, junction to case	per IGBT		R_{thJC}		0.120	K/W	
Thermal resistance, case to heatsink	per IGBT $\lambda_{\text{Paste}} = 1\text{ W}/(\text{m}\cdot\text{K}) / \lambda_{\text{grease}} = 1\text{ W}/(\text{m}\cdot\text{K})$		R_{thCH}	0.0800		K/W	
Temperature under switching conditions	$t_{op\text{ continuous}}$ $t_{op\text{ max}} 30\text{h over life time, for 10s within period of 10min}$		$T_{vj\text{ op}}$	-40 150	150 175	$^{\circ}\text{C}$	

¹⁾ DC-collector current limited by power terminals.

²⁾ DC-collector current limited by internal busbar.

3 Diode, Inverter

3.1 Maximum Rated Values

Parameter	Conditions	Symbol	Value	Unit
Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{RRM}	705	V
Continuous DC forward current		I_F	400 ¹⁾	A
Maximum RMS module terminal current		I_{RMS}	800	A
Repetitive peak forward current	$t_p = 1 \text{ ms}$	I_{FRM}	800	A
I^2t - value	$V_R = 0 \text{ V}, t_p = 10 \text{ ms}, T_{vj} = 125^{\circ}\text{C}$	I^2t	8800	A^2s
	$V_R = 0 \text{ V}, t_p = 10 \text{ ms}, T_{vj} = 150^{\circ}\text{C}$		8500	A^2s

3.2 Characteristic Values

Parameter	Conditions	Symbol	min. typ. max.			Unit	
Forward voltage	$I_F = 400 \text{ A}, V_{GE} = 0 \text{ V}$ $I_F = 400 \text{ A}, V_{GE} = 0 \text{ V}$ $I_F = 400 \text{ A}, V_{GE} = 0 \text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	V_F		1.55 1.50 1.45	1.95	V
Peak reverse recovery current	$I_F = 400 \text{ A}, -di_F/dt = 4500 \text{ A}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $V_R = 300 \text{ V}$ $V_{GE} = -15 \text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	I_{RM}		205 295 305		A
Recovered charge	$I_F = 400 \text{ A}, -di_F/dt = 4500 \text{ A}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $V_R = 300 \text{ V}$ $V_{GE} = -15 \text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	Q_r		15.0 32.0 34.0		μC
Reverse recovery energy	$I_F = 400 \text{ A}, -di_F/dt = 4500 \text{ A}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $V_R = 300 \text{ V}$ $V_{GE} = -15 \text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{rec}		3.35 6.90 8.10		mJ
Thermal resistance, junction to case	per diode		R_{thJC}			0.200	K/W
Thermal resistance, case to heatsink	per diode $\lambda_{Paste} = 1 \text{ W}/(\text{m}\cdot\text{K}) / \lambda_{grease} = 1 \text{ W}/(\text{m}\cdot\text{K})$		R_{thCH}		0.0850		K/W
Temperature under switching conditions	t_{op} continuous		$T_{vj op}$	-40		150	$^{\circ}\text{C}$
	$t_{op max}$ 30h over life time, for 10s within period of 10min			150		175	

4 NTC-Thermistor

Parameter	Conditions	Symbol	min. typ. max.			Unit
Rated resistance	$T_C = 25^{\circ}\text{C}$	R_{25}		5.00		$\text{k}\Omega$
Deviation of R100	$T_C = 100^{\circ}\text{C}, R_{100} = 493 \Omega$	$\Delta R/R$	5		5	%
Power dissipation	$T_C = 25^{\circ}\text{C}$	P_{25}			20.0	mW
B-value	$R_2 = R_{25} \exp [B_{25/50}(1/T_2 - 1/(298,15 \text{ K}))]$	$B_{25/50}$		3375		K
B-value	$R_2 = R_{25} \exp [B_{25/80}(1/T_2 - 1/(298,15 \text{ K}))]$	$B_{25/80}$		3411		K
B-value	$R_2 = R_{25} \exp [B_{25/100}(1/T_2 - 1/(298,15 \text{ K}))]$	$B_{25/100}$		3433		K

Specification according to the valid application note.

¹⁾ Diode forward current limited by power terminals.

5 Module

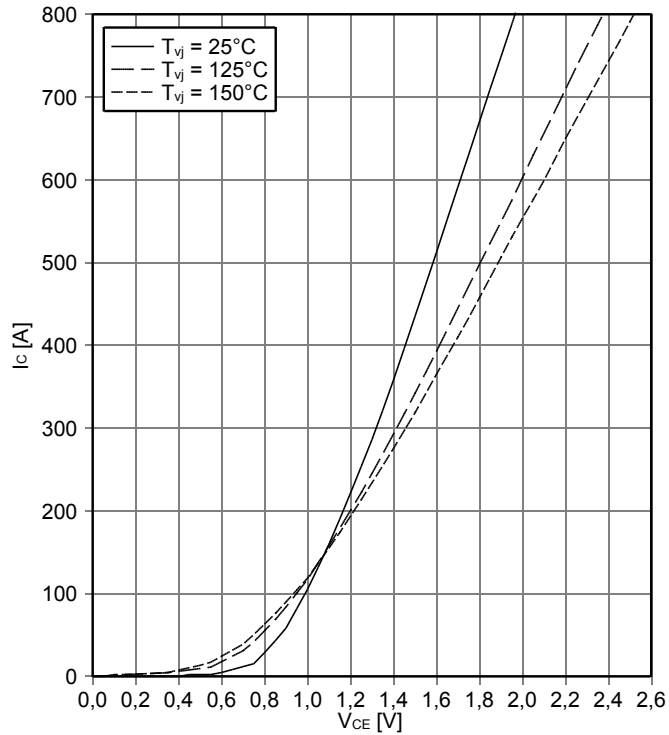
Parameter	Conditions	Symbol	Value			Unit
Isolation test voltage	RMS, f = 50 Hz, t = 1 min.	V_{ISOL}	2.5			kV
Material of module baseplate			Cu			
Internal isolation	basic insulation (class 1, IEC 61140)		Al ₂ O ₃			
Creepage distance	terminal to heatsink	d_{Creep}	12.0			mm
	terminal to terminal		6.1			
Clearance	terminal to heatsink	d_{Clear}	12.0			mm
	terminal to terminal		6.1			
Comperative tracking index		CTI	> 200			
			min.	typ.	max.	
Stray inductance module		L_{sCE}		15		nH
Module lead resistance, terminals - chip	$T_C = 25\text{ °C}$, per switch	R_{CC+EE}		1.00		mΩ
Storage temperature		T_{stg}	-40		125	°C
Mounting torque for modul mounting	Screw M5 baseplate to heatsink	M	3.00 ¹⁾		6.00 ¹⁾	Nm
Terminal connection torque	Screw M6	M	3.0 ¹⁾	-	6.0 ¹⁾	Nm
Weight		G		510		g

¹⁾ Mounting according to valid application note AN 2010-08 Mounting Instruction HybridPACK 1.

6 Characteristics Diagrams

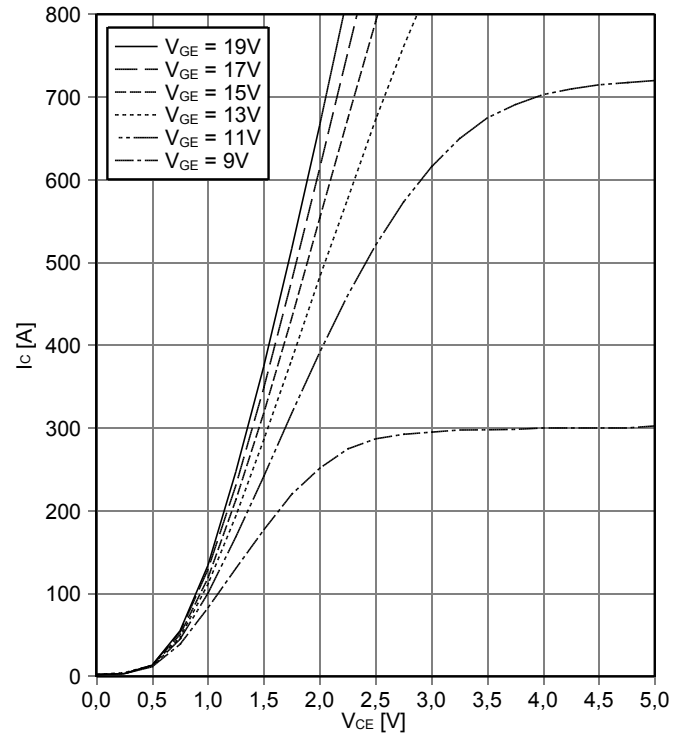
output characteristic IGBT, Inverter (typical)

$I_C = f(V_{CE})$
 $V_{GE} = 15\text{ V}$



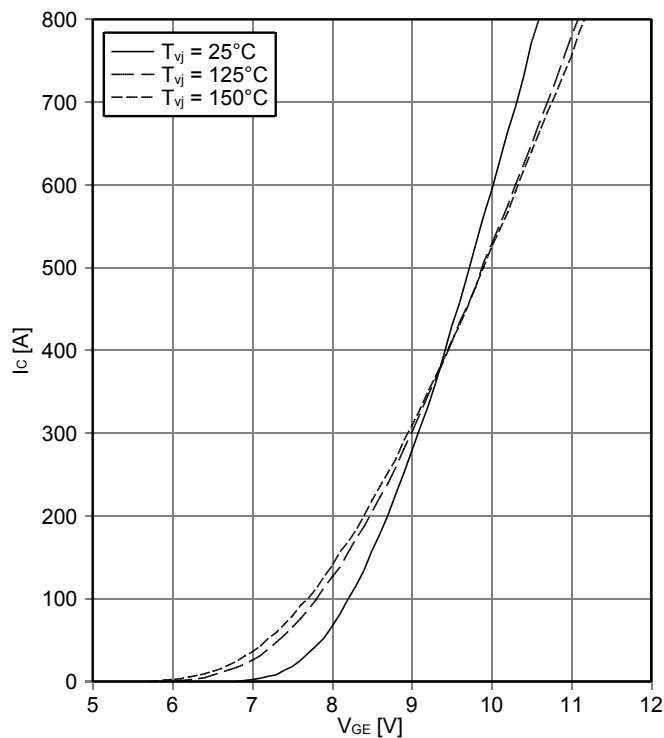
output characteristic IGBT, Inverter (typical)

$I_C = f(V_{CE})$
 $T_{vj} = 150^\circ\text{C}$



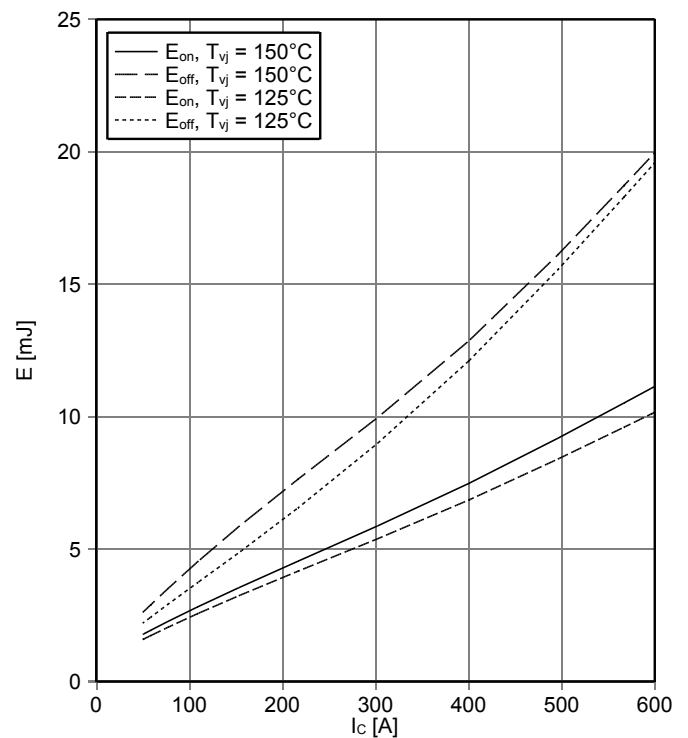
transfer characteristic IGBT, Inverter (typical)

$I_C = f(V_{GE})$
 $V_{CE} = 20\text{ V}$



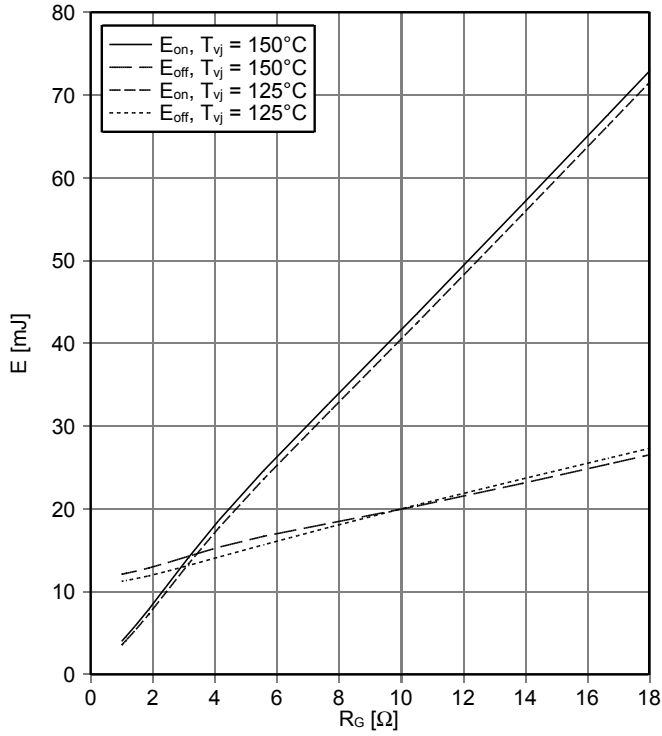
switching losses IGBT, Inverter (typical)

$E_{on} = f(I_C)$, $E_{off} = f(I_C)$
 $V_{GE} = \pm 15\text{ V}$, $R_{Gon} = 1,8\ \Omega$, $R_{Goff} = 400\ \Omega$, $V_{CE} = 300\text{ V}$



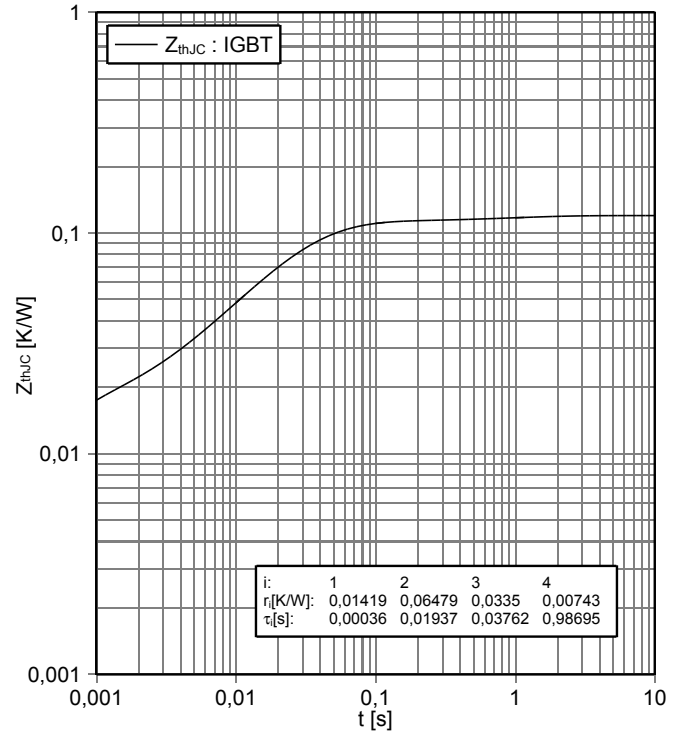
switching losses IGBT, Inverter (typical)

$E_{on} = f(R_G)$, $E_{off} = f(R_G)$
 $V_{GE} = \pm 15\text{ V}$, $I_C = 400\text{ A}$, $V_{CE} = 300\text{ V}$



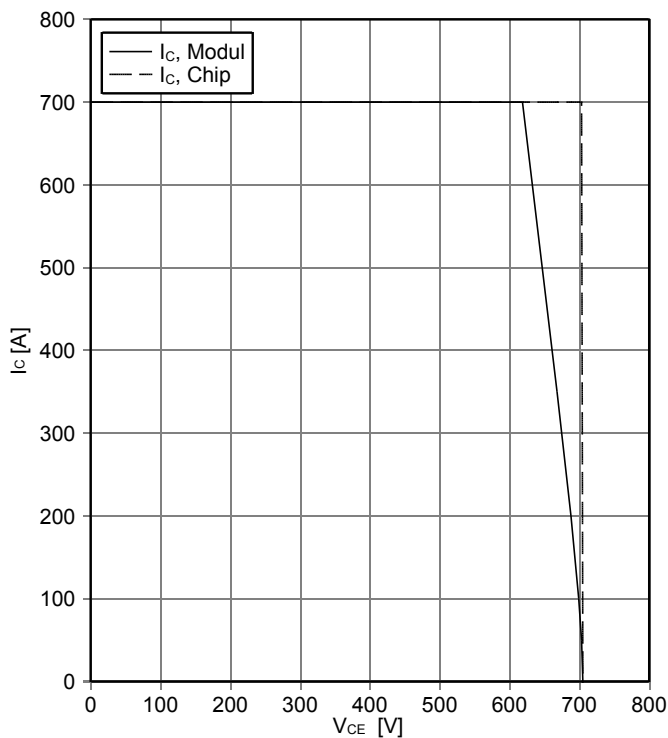
transient thermal impedance IGBT, Inverter

$Z_{thJC} = f(t)$



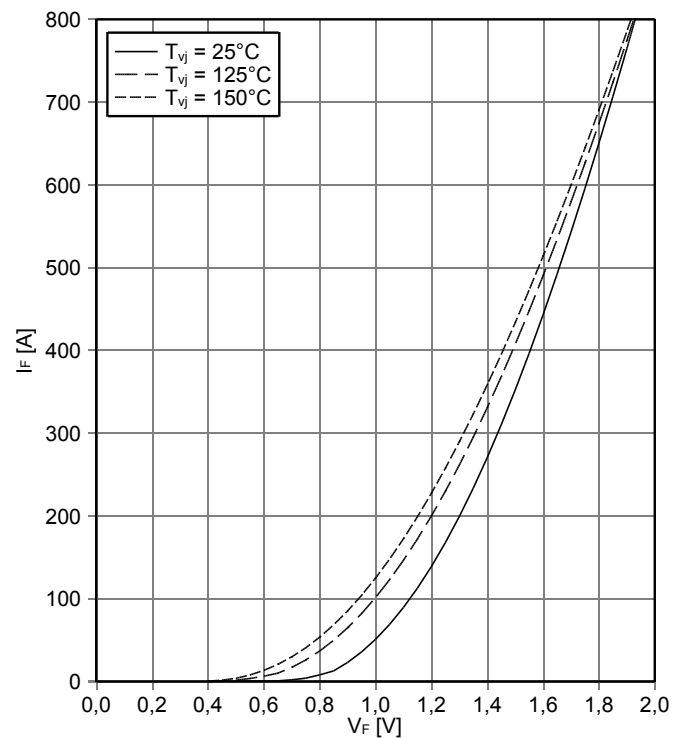
reverse bias safe operating area IGBT, Inverter (RBSOA)

$I_C = f(V_{CE})$
 $V_{GE} = \pm 15\text{ V}$, $R_{Goff} = 1,8\ \Omega$, $T_{vj} = 150^\circ\text{C}$



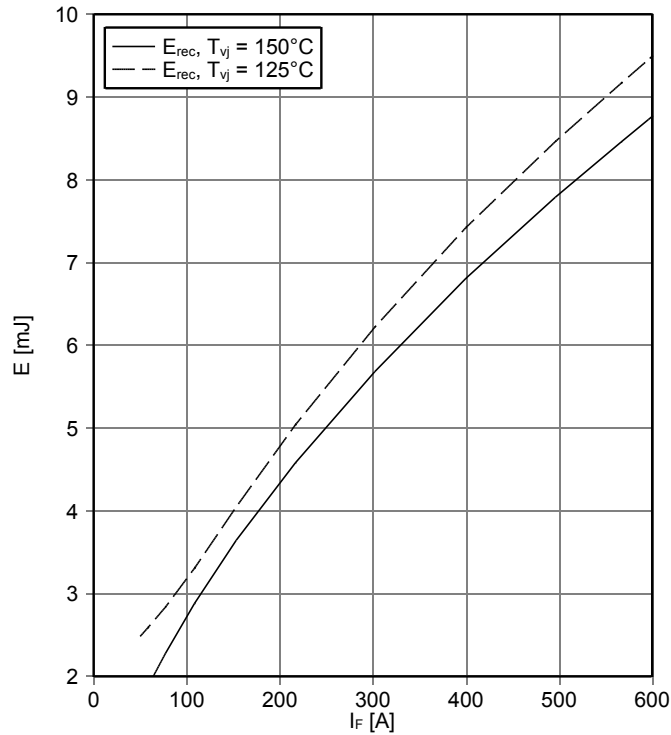
forward characteristic of Diode, Inverter (typical)

$I_F = f(V_F)$



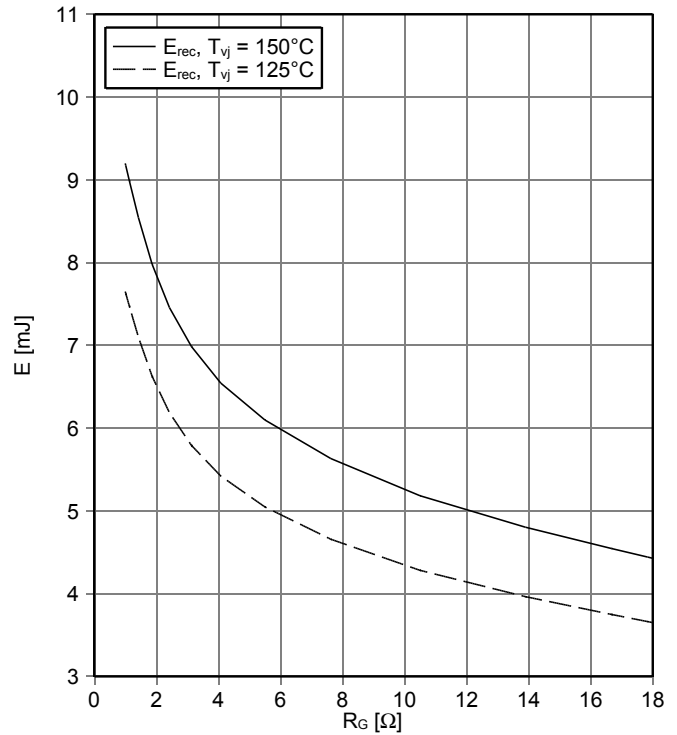
switching losses Diode, Inverter (typical)

$E_{rec} = f(I_F)$
 $R_{Gon} = 1,8 \Omega, V_{CE} = 300 V$



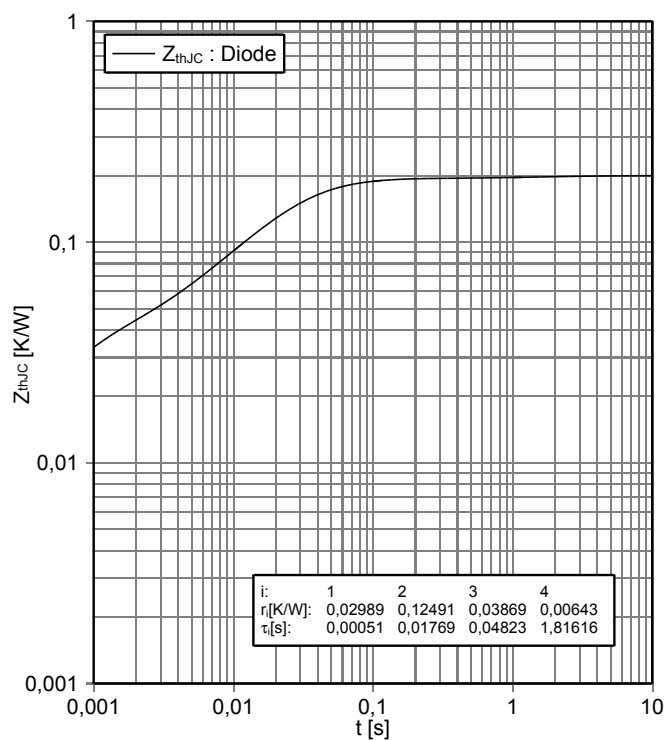
switching losses Diode, Inverter (typical)

$E_{rec} = f(R_G)$
 $I_F = 400 A, V_{CE} = 300 V$



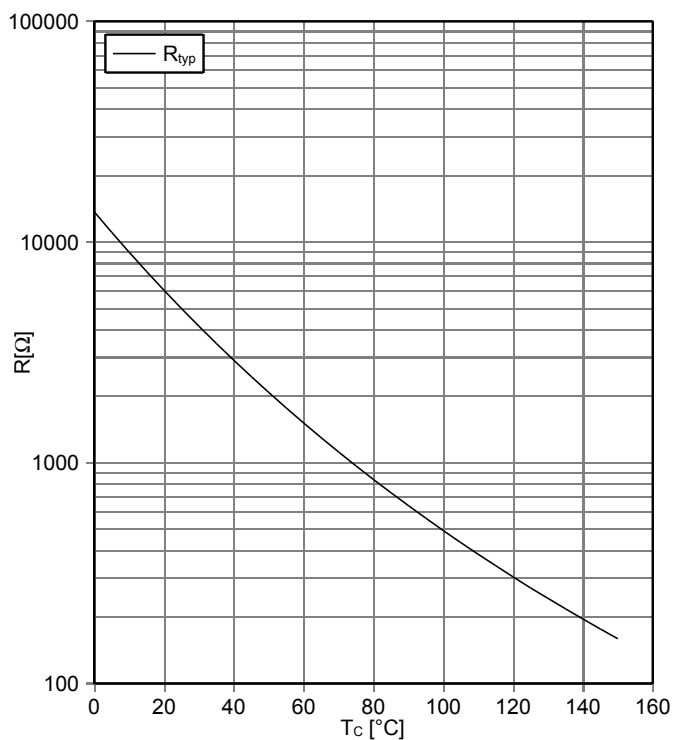
transient thermal impedance Diode, Inverter

$Z_{thJC} = f(t)$

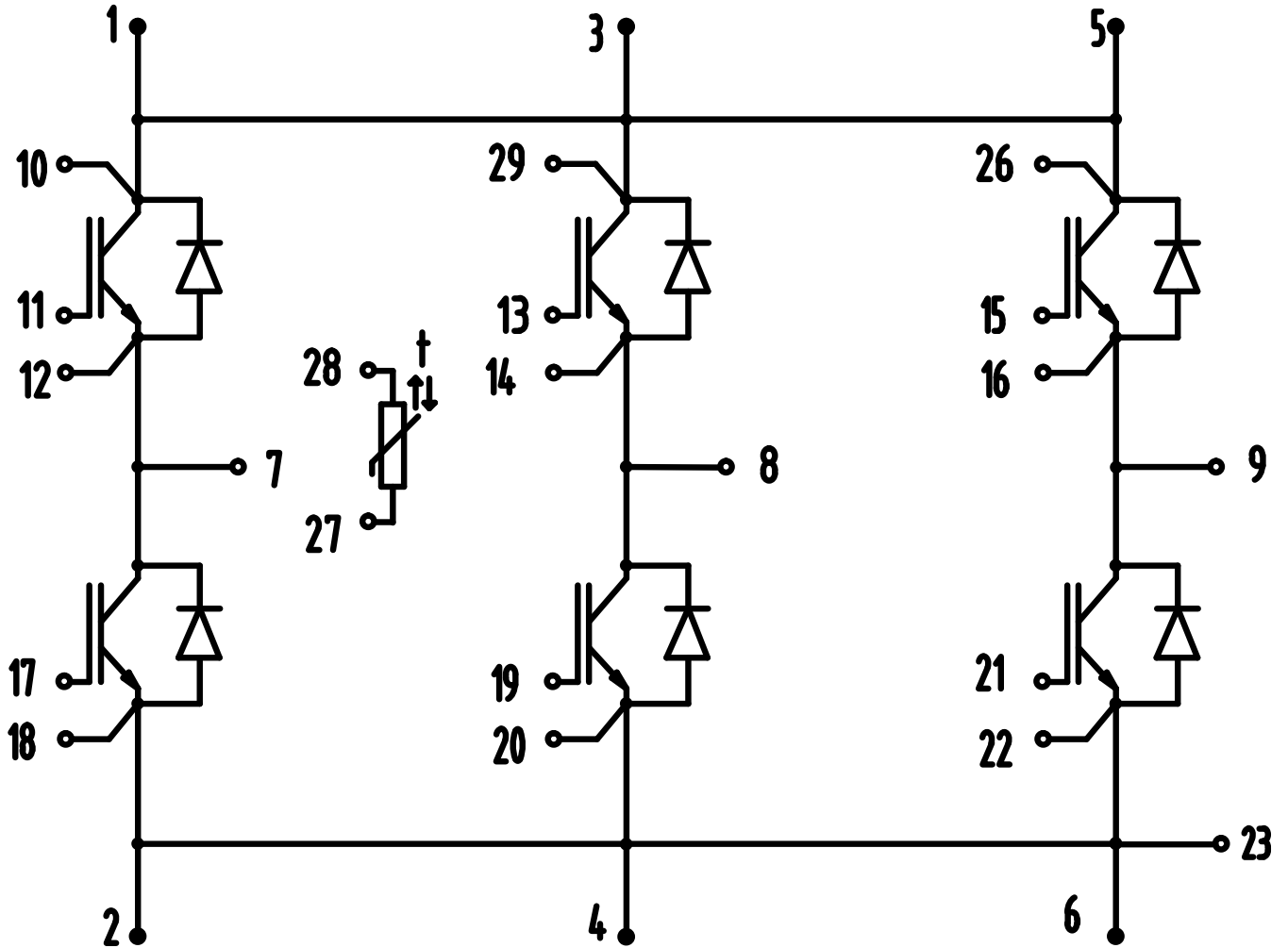


NTC-Thermistor-temperature characteristic (typical)

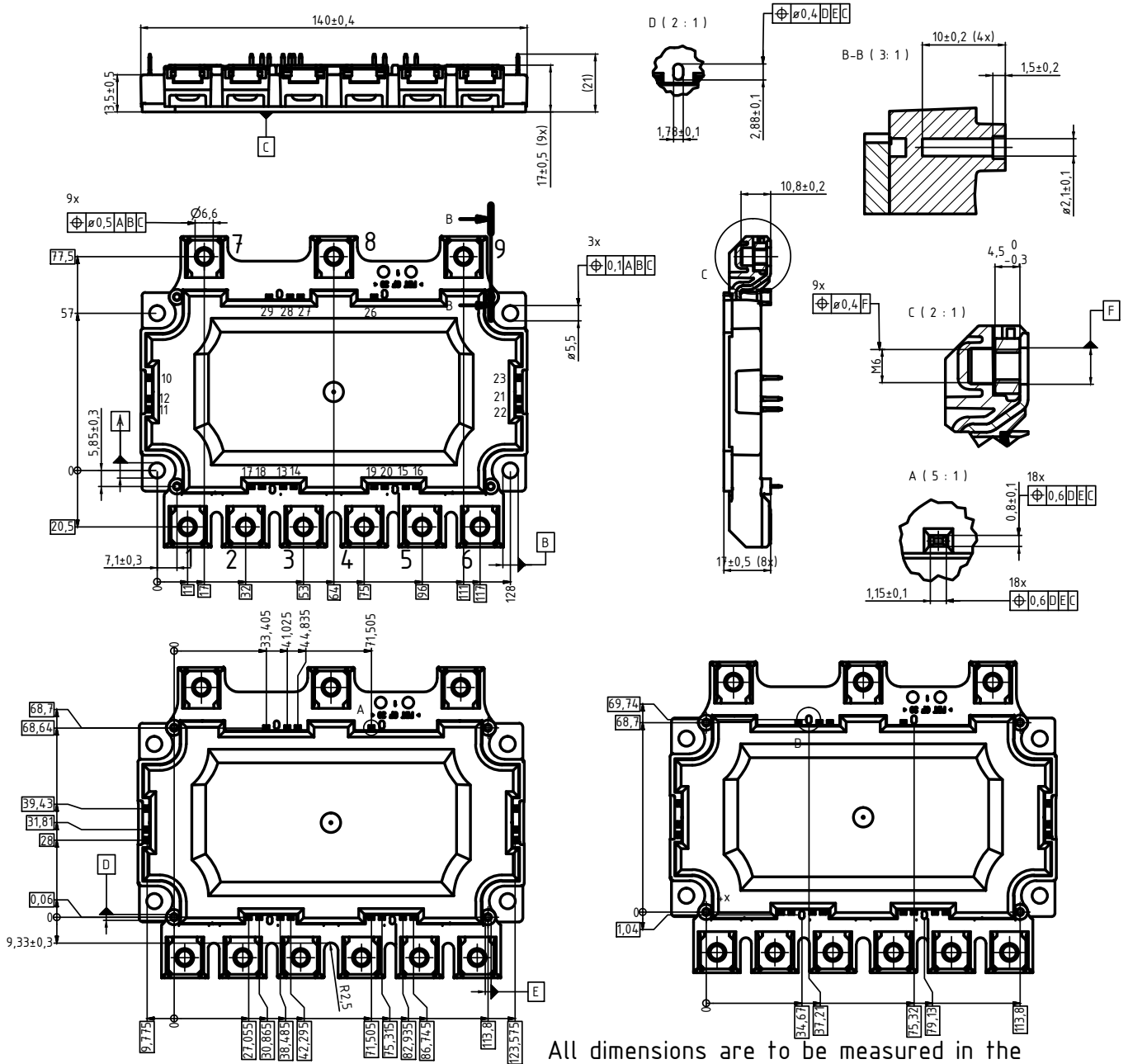
$R = f(T)$



7 Circuit diagram




8 Package outlines




All dimensions are to be measured in the mounted condition

9 Label Codes

9.1 Module Code

Code Format	Data Matrix		
Encoding	ASCII Text		
Symbol Size	16x16		
Standard	IEC24720 and IEC16022		
Code Content	Content Module Serial Number Module Material Number Production Order Number Datecode (Production Year) Datecode (Production Week)	Digit 1 - 5 6 - 11 12 - 19 20 - 21 22 - 23	Example (below) 71549 142846 55054991 15 30
Example	 71549142846550549911530		

9.2 Packing Code

Code Format	Code128			
Encoding	Code Set A			
Symbol Size	34 digits			
Standard	IEC8859-1			
Code Content	Content Backend Construction Number Production Lot Number Serial Number Date Code Box Quantity	Identifier X 1T S 9D Q	Digit 2 - 9 12 - 19 21 - 25 28 - 31 33 - 34	Example (below) 95056609 2X0003E0 754389 1139 15
Example	 X950566091T2X0003E0S754389D1139Q15			



Revision History

Major changes since previous revision

Revision History

Reference	Date	Description
V1.0	2015-04-24	-
V2.0	2015-11-09	-
V3.0	2017-03-07	-

Terms & Conditions of usage

Edition 2014-05-30

Published by
Infineon Technologies AG
81726 Munich, Germany
 © 2014 Infineon Technologies AG
All Rights Reserved.

Legal Disclaimer

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics. With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation, warranties of non-infringement of intellectual property rights of any third party.

Information

For further information on technology, delivery terms and conditions and prices, please contact the nearest Infineon Technologies Office (<http://www.infineon.com>)

Warnings

Due to technical requirements, components may contain dangerous substances. For information on the types in question, please contact the nearest Infineon Technologies Office.

Infineon Technologies components may be used in life-support devices or systems only with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.

Trademarks

Trademarks of Infineon Technologies AG

AURIX™, C166™, CanPAK™, CIPOS™, CIPURSE™, EconoPACK™, CoolMOS™, CoolSET™, CORECONTROL™, CROSSAVE™, DAVE™, DI-POL™, EasyPIM™, EconoBRIDGE™, EconoDUAL™, EconoPIM™, EconoPACK™, EiceDRIVER™, eupec™, FCOS™, HITFET™, HybridPACK™, I²RF™, ISOFACE™, IsoPACK™, MIPAQ™, ModSTACK™, my-d™, Novalithic™, OptiMOS™, ORIGA™, POWERCODE™, PRIMARION™, PrimePACK™, PrimeSTACK™, PRO-SIL™, PROFET™, RASIC™, ReverSave™, SatRIC™, SIEGET™, SINDRION™, SIPMOS™, SmartLEWIS™, SOLID FLASH™, TEMPFET™, thinQ!™, TRENCHSTOP™, TriCore™.

Other Trademarks

Advance Design System™ (ADS) of Agilent Technologies, AMBA™, ARM™, MULTI-ICE™, KEIL™, PRIMECELL™, REALVIEW™, THUMB™, μVision™ of ARM Limited, UK. AUTOSAR™ is licensed by AUTOSAR development partnership. Bluetooth™ of Bluetooth SIG Inc. CAT-iq™ of DECT Forum. COLOSSUS™, FirstGPS™ of Trimble Navigation Ltd. EMV™ of EMVCo, LLC (Visa Holdings Inc.). EPCOS™ of Epcos AG. FLEXGO™ of Microsoft Corporation. FlexRay™ is licensed by FlexRay Consortium. HYPERTERMINAL™ of Hilgraeve Incorporated. IEC™ of Commission Electrotechnique Internationale. IrDA™ of Infrared Data Association Corporation. ISO™ of INTERNATIONAL ORGANIZATION FOR STANDARDIZATION. MATLAB™ of MathWorks, Inc. MAXIM™ of Maxim Integrated Products, Inc. MICROTEC™, NUCLEUS™ of Mentor Graphics Corporation. MIPI™ of MIPI Alliance, Inc. MIPS™ of MIPS Technologies, Inc., USA. muRata™ of MURATA MANUFACTURING CO., MICROWAVE OFFICE™ (MWO) of Applied Wave Research Inc., OmniVision™ of OmniVision Technologies, Inc. Openwave™ Openwave Systems Inc. RED HAT™ Red Hat, Inc. RFMD™ RF Micro Devices, Inc. SIRIUS™ of Sirius Satellite Radio Inc. SOLARIS™ of Sun Microsystems, Inc. SPANSION™ of Spansion LLC Ltd. Symbian™ of Symbian Software Limited. TAIYO YUDEN™ of Taiyo Yuden Co. TEAKLITE™ of CEVA, Inc. TEKTRONIX™ of Tektronix Inc. TOKO™ of TOKO KABUSHIKI KAISHA TA. UNIX™ of X/Open Company Limited. VERILOG™, PALLADIUM™ of Cadence Design Systems, Inc. VLYNQ™ of Texas Instruments Incorporated. VXWORKS™, WIND RIVER™ of WIND RIVER SYSTEMS, INC. ZETEX™ of Diodes Zetex Limited.

Last update

2011-11-11

www.infineon.com

Published by Infineon Technologies AG

Downloaded From Oneyac.com

单击下面可查看定价，库存，交付和生命周期等信息

[>>Infineon Technologies\(英飞凌\)](#)